



SB820 THRU SB860 SCHOTTKY BARRIER RECTIFIER

TECHNICAL
SPECIFICATION

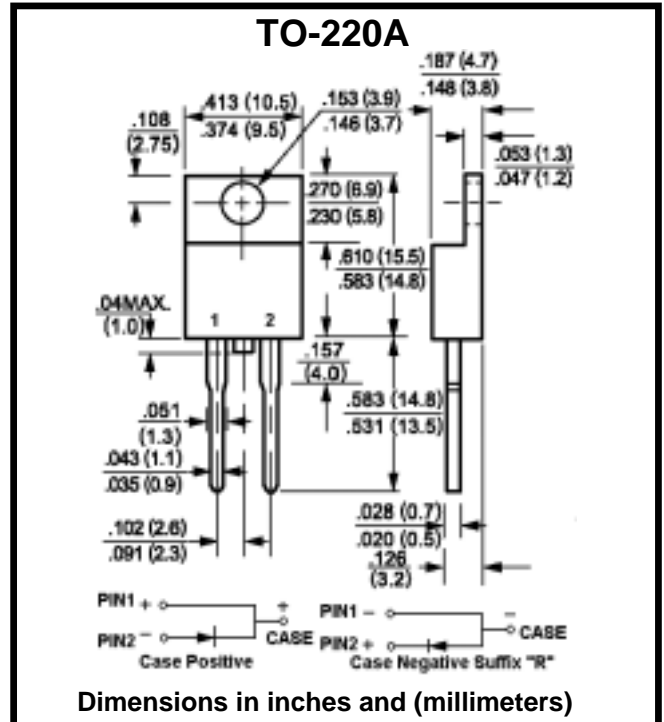
VOLTAGE: 20 TO 60V CURRENT: 8.0A

FEATURES

- Epitaxial construction for chip
- High current capability
- Low forward voltage drop
- Low power loss, high efficiency
- High surge capability
- High temperature soldering guaranteed:
250°C/10sec/0.375"(9.5mm) lead length
at 5 lbs tension

MECHANICAL DATA

- Terminal: Plated leads solderable per
MIL-STD 202E, method 208C
- Case: Molded with UL-94 Class V-O
recognized flame retardant epoxy
- Polarity: As marked
- Mounting position: Any



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Single-phase, half-wave, 60Hz, resistive or inductive load rating at 25°C, unless otherwise stated, for capacitive load, derate current by 20%)

RATINGS	SYMBOL	SB 820	SB 830	SB 835	SB 840	SB 850	SB 860	UNITS
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	20	30	35	40	50	60	V
Maximum RMS Voltage	V_{RMS}	14	21	25	28	35	42	V
Maximum DC Blocking Voltage	V_{DC}	20	30	35	40	50	60	V
Maximum Average Forward Rectified Current ($T_C=95^\circ\text{C}$)	$I_{F(AV)}$	8.0						A
Peak Forward Surge Current (8.3ms single half sine-wave superimposed on rated load)	I_{FSM}	150						A
Maximum Forward Voltage (at 8.0A DC)	V_F	0.65			0.75			V
Maximum DC Reverse Current $T_a=25^\circ\text{C}$ (at rated DC blocking voltage) $T_a=100^\circ\text{C}$	I_R	5.0 50.0						mA mA
Typical Junction Capacitance (Note 1)	C_J	700			450			pF
Typical Thermal Resistance (Note 2)	$R_\theta(ja)$	2.5						$^\circ\text{C/W}$
Operating Junction Temperature	T_J	-65 to +125			-65 to +150			$^\circ\text{C}$
Storage Temperature	T_{STG}	-65 to +150						$^\circ\text{C}$

Note:

1. Measured at 1.0 MHz and applied reverse voltage of 4.0Vdc
2. Thermal resistance from junction to case
3. Suffix "R" for reverse polarity